

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	62459	(a-si or asi or ((amorphous or alpha) near2 (si or silicon)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/30 11:06
2	BRS	L2	1946	1 near8 (PVD or "physical vapor deposition" or sputter\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/30 12:25
3	BRS	L6	68600	(aluminum or ITO or "indium tin oxide" or nickel or ni or cobalt or co or Al or palladium or pd or germanium or Ge) near8 crystal\$6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/30 11:18
4	BRS	L8	105957	polysilicon or poly-silicon or polysi or poly-si or (poly near2 (si or silicon))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/30 11:19
5	BRS	L9	109439 6	crystal\$6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/30 11:20

	Type	L #	Hits	S arch Text	DBs	Time Stamp
6	BRS	L10	403	6 near8 8 near8 9	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/30 12:27
7	BRS	L11	305	6 near8 9 near8 8	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/30 11:21
8	BRS	L12	31	2 and 11	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/30 11:21
9	BRS	L13	52151	(TFT or "thin film transistor" or T-F-T)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/30 11:22
10	BRS	L14	24	12 and 13	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/30 12:24

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L15	14799	(metal adj induc\$4 adj crystal\$6) or MIC	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/30 12:25
12	BRS	L16	2	14 and 15	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/30 12:25
13	BRS	L17	743	6 same 9 same 8	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/30 12:27
14	BRS	L18	43	2 and 17	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/12/30 12:27